

2SA2082

Silicon PNP epitaxial planar type

For high speed switching

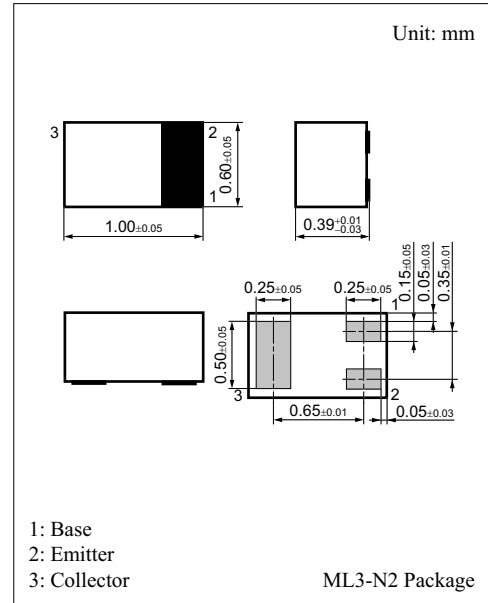
■ Features

- High speed switching
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Suitable for high-density mounting and downsizing of the equipment for ultraminiature leadless package

Package: 0.6 mm × 1.0 mm (height 0.39 mm)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-10	V
Collector-emitter voltage (Base open)	V_{CEO}	-10	V
Emitter-base voltage (Collector open)	V_{EBO}	-4	V
Collector current	I_C	-50	mA
Peak collector current	I_{CP}	-100	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

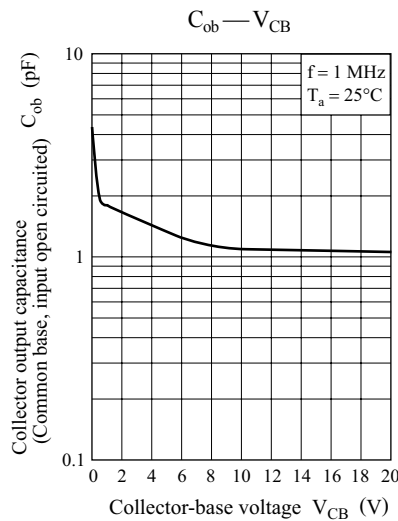
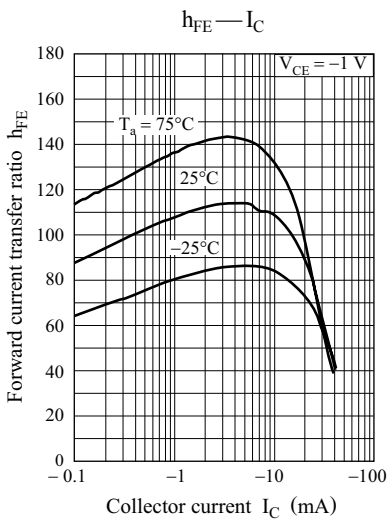
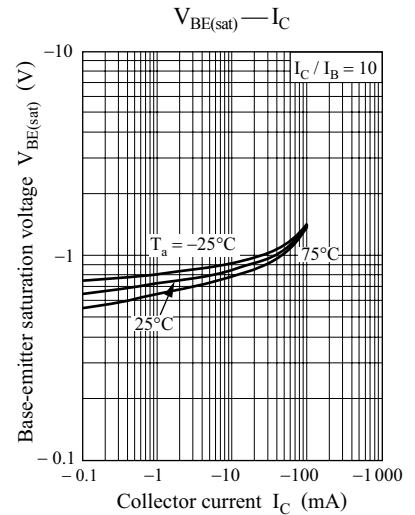
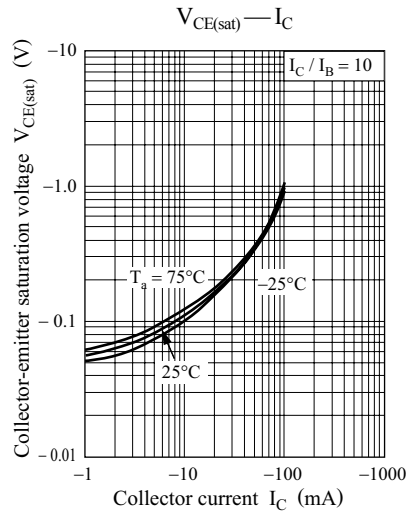
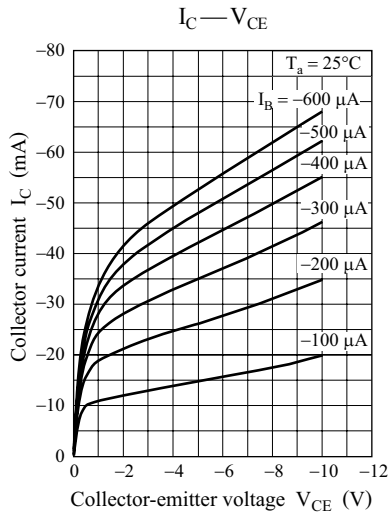
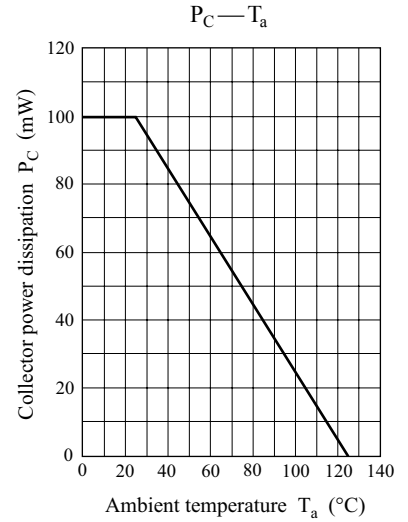
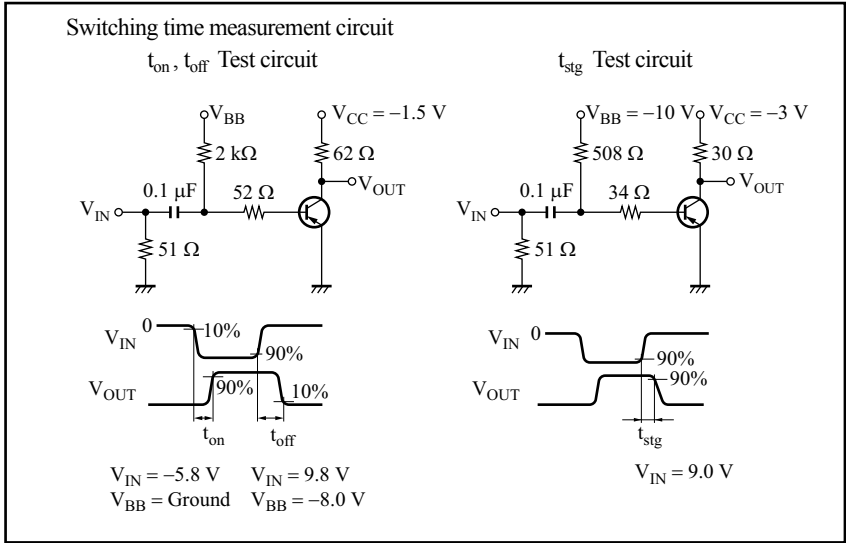


Marking Symbol : 4N

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -8\text{ V}, I_E = 0$			-0.1	μA
Emitter-base cut-off current (Collector open)	I_{EBO}	$V_{EB} = -3\text{ V}, I_C = 0$			-0.1	μA
Forward current transfer ratio	h_{FE1}	$V_{CE} = -1\text{ V}, I_C = -10\text{ mA}$	50		150	—
	h_{FE2}	$V_{CE} = -1\text{ V}, I_C = -1\text{ mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{ mA}, I_B = -1\text{ mA}$		-0.1	-0.2	V
Transition frequency	f_T	$V_{CB} = -10\text{ V}, I_E = 10\text{ mA}, f = 200\text{ MHz}$	800	1 500		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -5\text{ V}, I_E = 0, f = 1\text{ MHz}$		2.2		pF
Turn-on time	t_{on}	Switching time measurement circuit		12		ns
Turn-off time	t_{off}			20		ns
Storage time	t_s			19		ns

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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